

EE610A Analog VLSI Circuits

Project Report

Course: EE610A Analog VLSI Circuits

Project: Differential Amplifier Design

Instructor: Prof. Imon Mondal

Student Name: Shital Niras

Roll Number: 230967

Date: 03 July, 2025

1. Abstract

This report presents the design and simulation of a single-stage differential amplifier using a pMOS input stage for a non-inverting amplifier configuration. The goal was to achieve a loop gain ≥ 40 dB, bandwidth ≥ 25 MHz, and CMRR ≥ 80 dB using Cadence Virtuoso and 45nm GPDK. This report details the design approach, theoretical calculations, simulation results, and temperature performance from 0°C to 70°C.

2. Design Specifications

Parameter	Value
Input Stage	pMOS
VDD	1.8 V
Load Capacitance (CL)	20 pF
Minimum Loop Gain	40 dB
Minimum Bandwidth	25 MHz
Minimum CMRR	80 dB

3. Design Approach

3.1 Determining Transconductance (gm)

Using the unity-gain bandwidth relation:

$$f_{\text{unity}} = g_m / (2\pi * CL)$$

Given:

- $CL = 20 \text{ pF}$
- Required -3 dB bandwidth $\geq 25 \text{ MHz}$

We compute:

$$g_m = 2\pi \times 25 \text{ MHz} \times 20 \text{ pF} \approx 6.28 \text{ mS}$$

Hence, **$g_m \geq 6.28 \text{ mS}$** is required for the input differential pair.

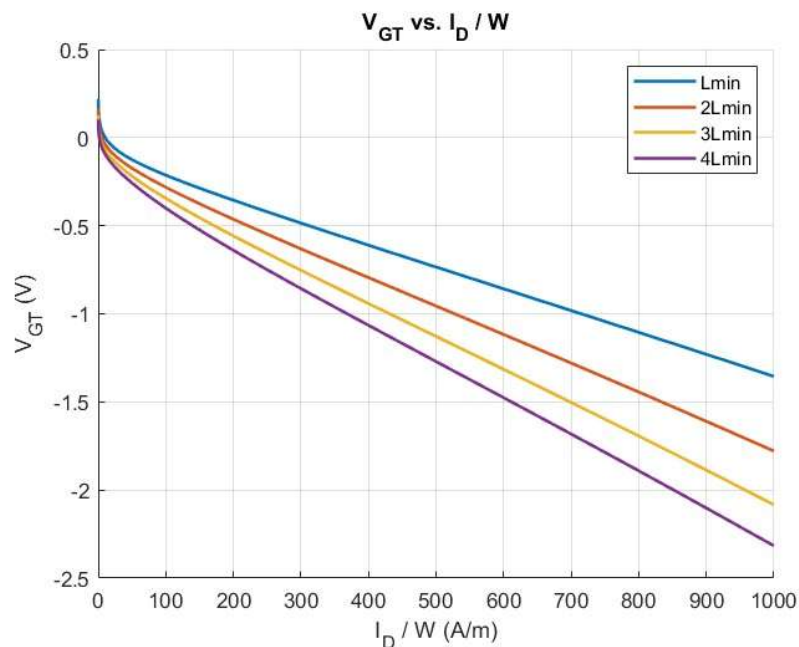
3.2 Using Lookup Tables for Parameter Selection

DC simulations were performed in Cadence ADE to extract g_m , g_{ds} , I_D , and V_{GT} . These were exported to CSV and plotted externally.

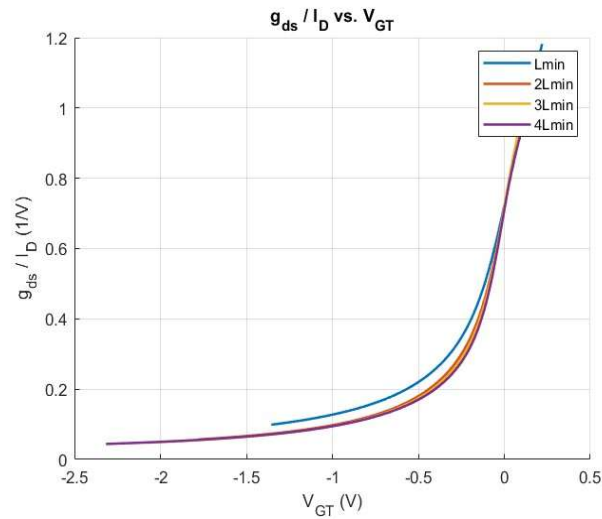
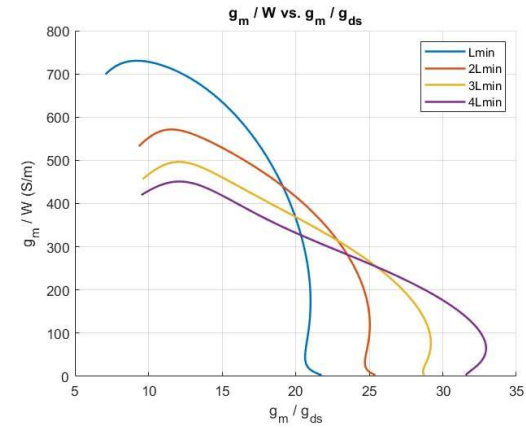
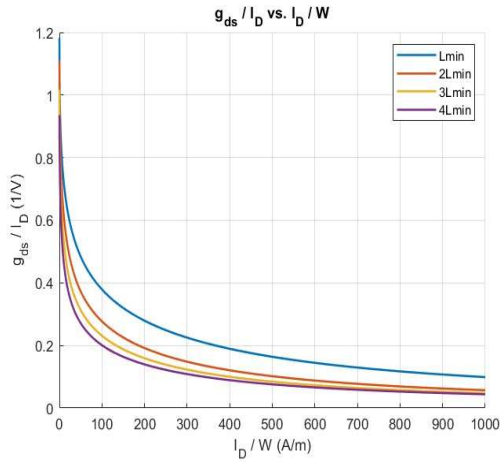
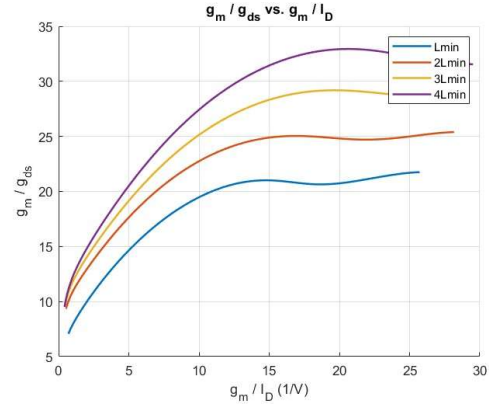
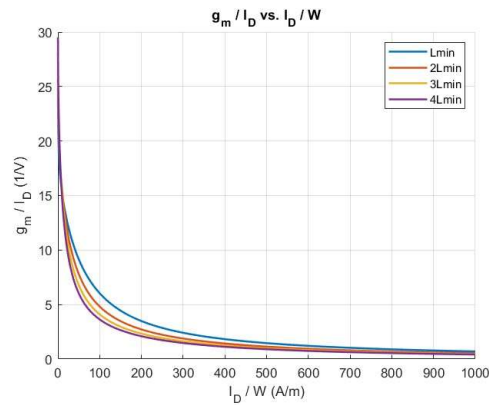
Graphs were analyzed to select points with high g_m , good g_m/g_{ds} (intrinsic gain), and moderate V_{ov} .

Graphs for PMOS were attached;

NMOS were evaluated



similarly



3.3 Loop Gain and Intrinsic Gain Requirement

In a negative feedback system:

$$\text{Loop Gain} = A_{DM} \times \beta$$

For $\beta = 0.5$ and Loop Gain > 100 :
 $A_{DM} > 200$

$$A_{DM} = g_m \times (r_{o1} \parallel r_{o2})$$

$$\text{Assuming } r_{o1} = r_{o2} \Rightarrow A_{DM} = g_m \times r_o / 2 \Rightarrow g_m/g_{ds} > 400$$

This was infeasible with a basic differential pair. Thus, we chose a cascode configuration.

3.4 Cascode Configuration

For cascode:

$$A_{DM} \approx g_m \times (g_m \times r_o)^2$$

Target: $g_m/g_{ds} \geq 30$, $g_m \approx 8 \text{ mS}$

g_m -ID plots helped determine ID, V_{ov} , and W/L ratios.
Bias voltages and gate voltages were set accordingly.

3.5 Biasing and Sizing Strategy

Using g_m -ID and V_{ov} plots, we sized PMOS inputs for higher g_m without increasing current.
Biasing ensured cascode transistors remained in saturation.

3.6 Sizing of Other Transistors

Transistors PM4–PM7 (PMOS) and NM0–NM3 (NMOS) were sized using the required g_m and ID from graphs.

3.7 CMRR Consideration

To achieve high CMRR:

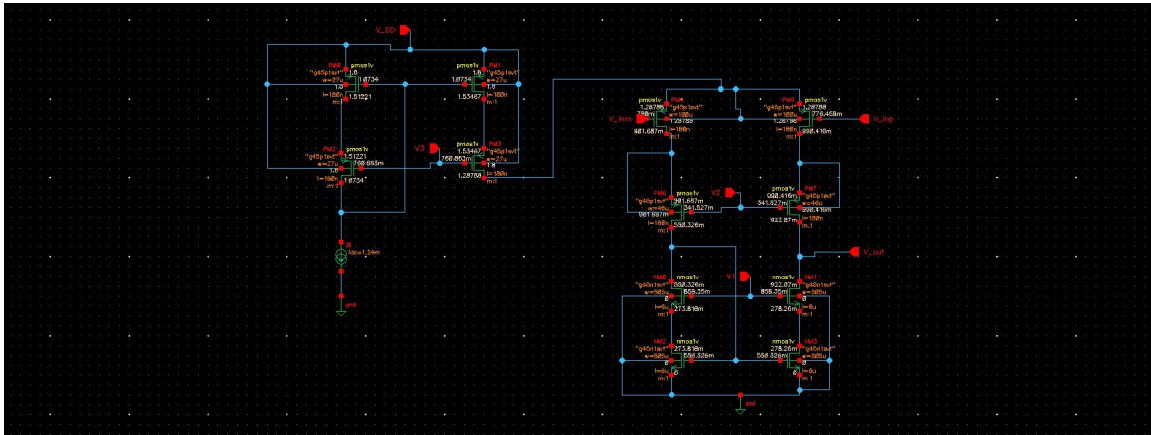
$$CMRR = A_{DM} / A_{CM} \approx g_m / g_{ds}$$

A_{CM} is approximately $1/(2 \cdot g_{mp} \cdot R_x)$ where R_x is output resistance of tail current source cascode configuration

$$R_x = g_m \cdot r_{o1} \cdot r_{o2}$$

Tail current source was cascoded. PM0–PM3 were sized carefully to maintain common-mode rejection and bias.

4. Schematic Diagram



5. Temperature Sweep Analysis

Temperature (° C)	Loop Gain (dB)	Bandwidth (MHz)	CMRR (dB)
0	42.382	29.75	90.4176
27	41.6892	27	88.6211
50	40.9641	25.8	86.5148
70	40.2076	24.49	84.33

6. DC Operating Point Results

Extracted from Cadence simulation (ADE → Results → Print → DC Operating Point):

Transistor	W/L (μm/μm)	gm (mS)	gds (μS)	Vov (V)	Cgs (fF)	Cgd (fF)
PM0	27 / 0.18	6.09	1.29m	-0.299	-53.7	-5.95
PM1	27 / 0.18	6.04	1.33m	-0.299	-53.69	-5.99
PM2	27 / 0.18	6.78	530.69	-0.288	-52.97	-5.45

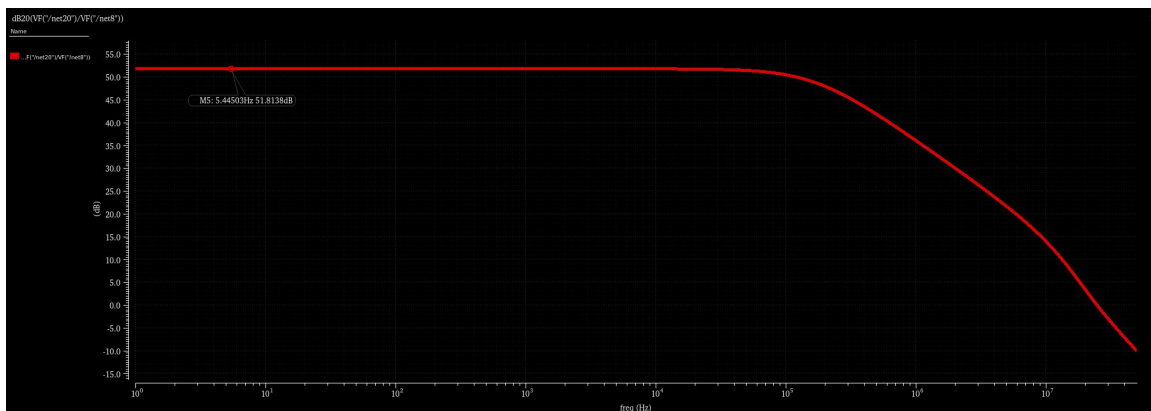
Transistor	W/L ($\mu\text{m}/\mu\text{m}$)	g_m (mS)	g_{ds} (μS)	V_{ov} (V)	C_{gs} (fF)	C_{gd} (fF)
PM3	27 / 0.18	6.54	700	-0.293	-53	-5.57
PM4	100 / 0.18	9.79	474.13	-0.088	-155	-20.37
PM5	100 / 0.18	9.79	473.33	-0.088	-155.184	-20.37
PM6	46 / 0.18	7.32	333.578	-0.135	-79.42	-9.2
PM7	46 / 0.18	7.32	329	-0.134	-79.38	-9.2
NM0	505 / 6	5.61	154.35	0.189	-28.81p	-720
NM1	505 / 6	5.61	162	0.189	-28.81p	-780
NM2	505 / 6	5.53	177.61	0.194	-29.53p	-795
NM3	505 / 6	5.53	177.82	0.194	-29.53p	-797

7. Simulation Results

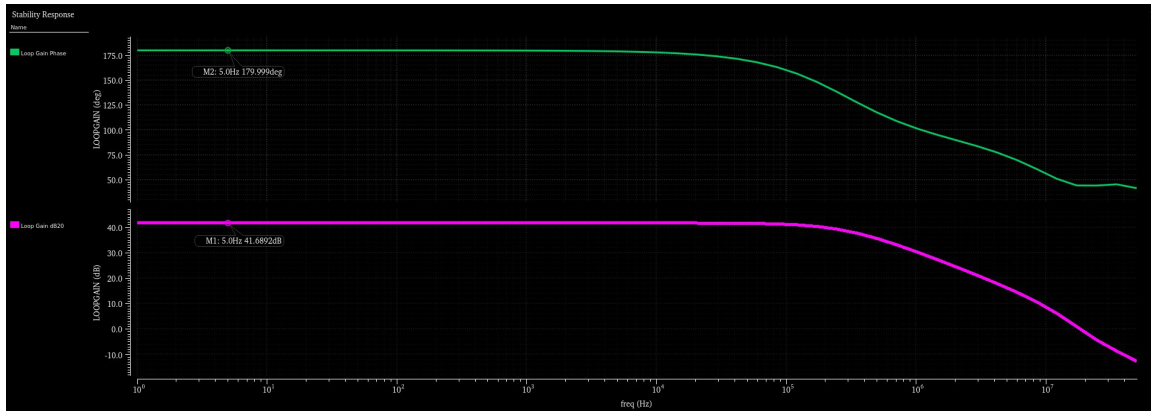
Include plots for:

- Open-loop gain and phase

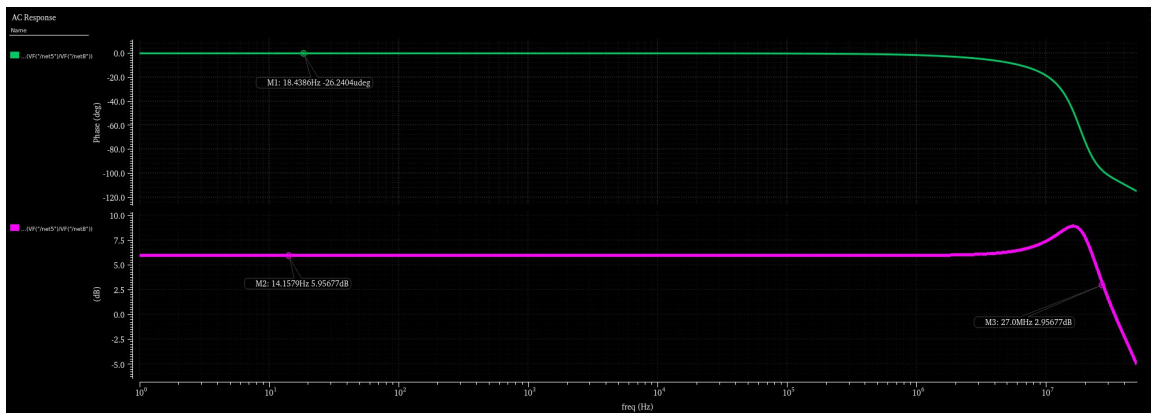
Adm Plot



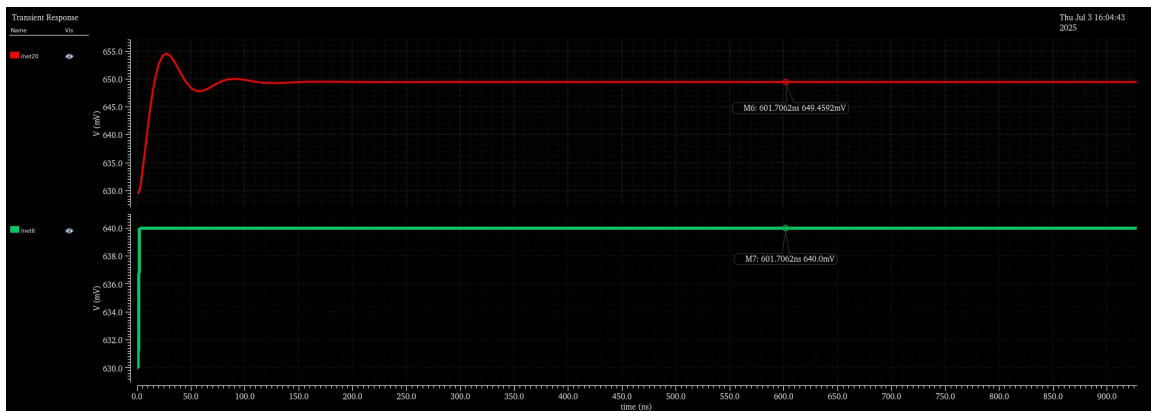
Loop gain and phase



- Closed-loop gain and phase



- Transient response with step input



Steady-State Error Analysis

A step input of **10 mV (0.01 V)** was applied with V_{bias} of 630mV to the non-inverting amplifier. The output settled at:

$V_{out, ss} = 649.4593 \text{ mV}$

The bias voltage was **640 mV**, so the actual output step is:

$$\Delta V_{out} = 649.4593 \text{ mV} - 640 \text{ mV} = \mathbf{9.4593 \text{ mV}}$$

Since the expected ideal output step is **10 mV**, the **simulated steady-state error** is:

$$SSE_{sim} = 0.01 \text{ V} - 0.0094593 \text{ V} = 0.0005407 \text{ V} = \mathbf{540.7 \text{ } \mu\text{V}}$$

Theoretical Steady-State Error

The loop gain from simulation is:

$$A_{loop} = 1041.6892 / 20 \approx 121.31$$

The theoretical SSE is:

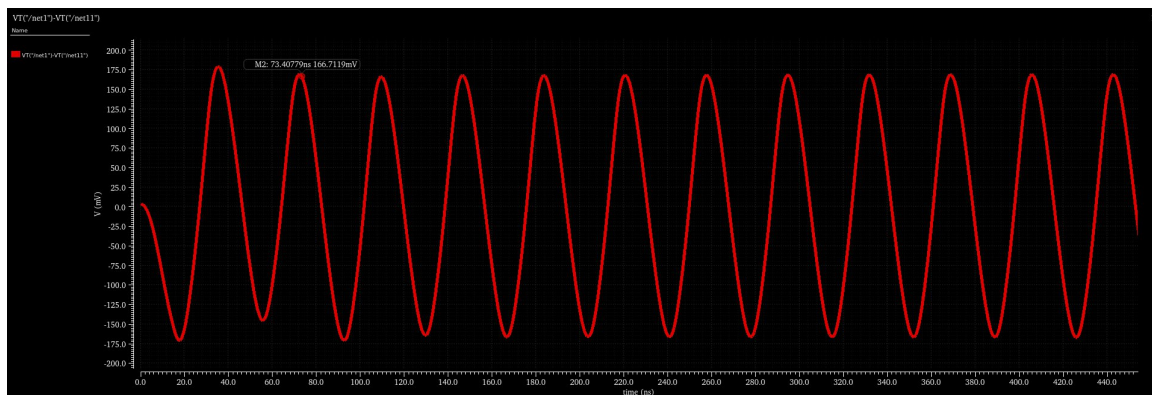
$$SSE_{theoretical} = 1 / (1 + A_{loop}) = 1 / (1 + 121.31) \approx 0.00818$$

For a 10 mV step input:

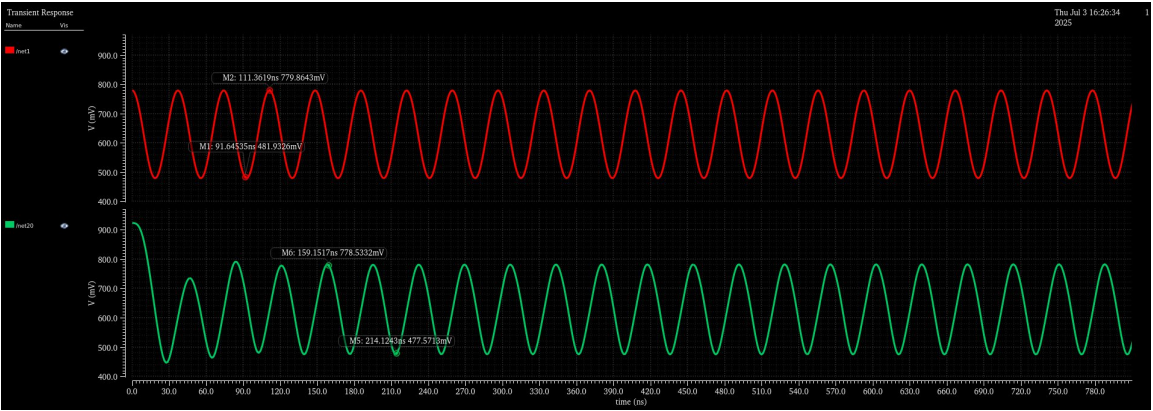
$$SSE_{theoretical} = 10 \text{ mV} \times 0.00818 \approx \mathbf{81.8 \text{ } \mu\text{V}}$$

- Transient response with 150 mV $\cos(\omega t)$ for $\omega = \omega_{3dB}$

V+ - V- plot

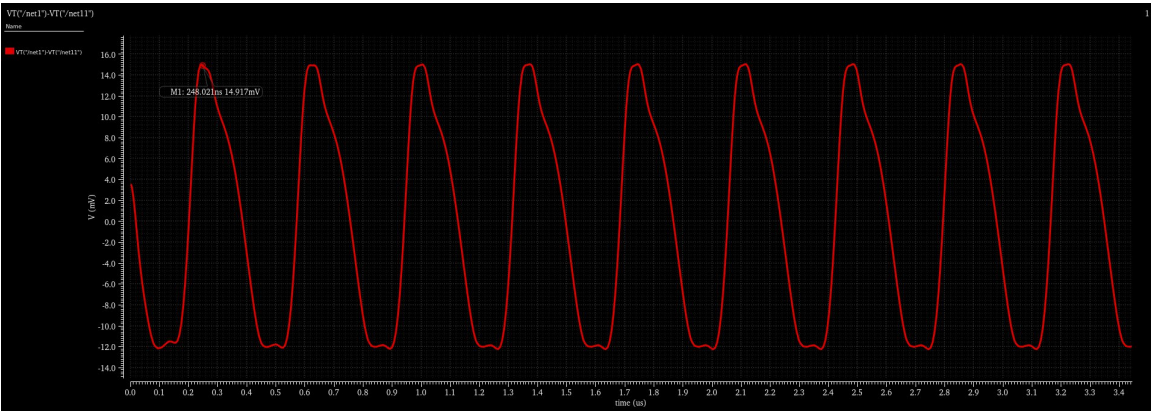


Input Output Plots

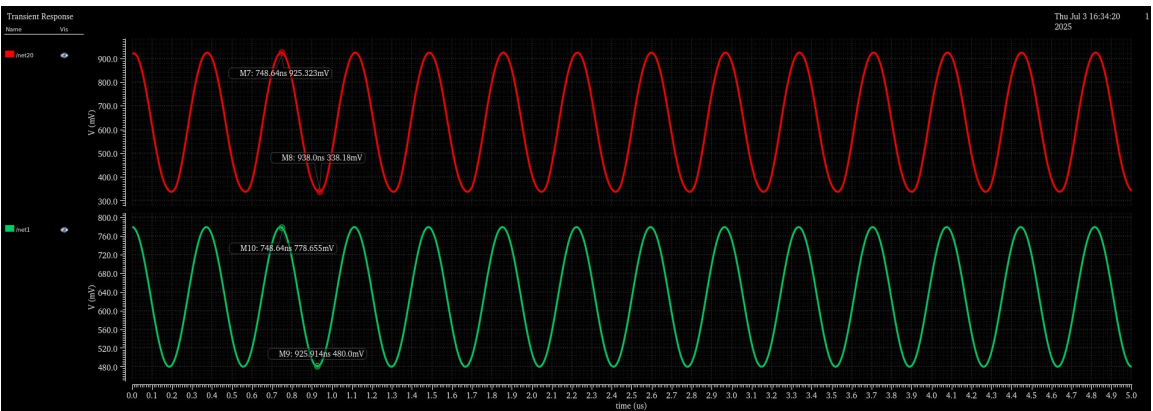


- Transient response with 150 mV cos(ωt) for $\omega = \omega_{3dB}/10$

V+ - V- plot



Input Output Plot

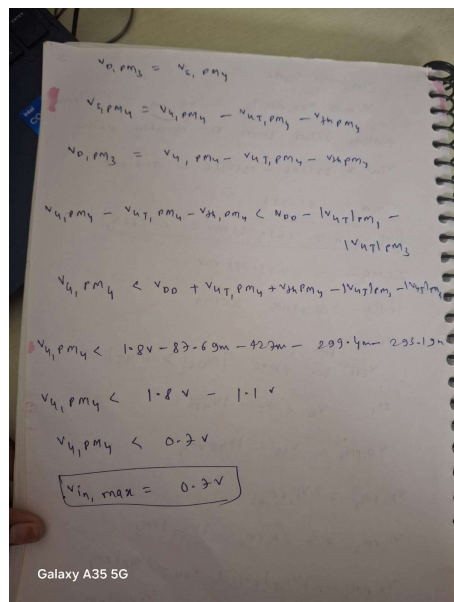
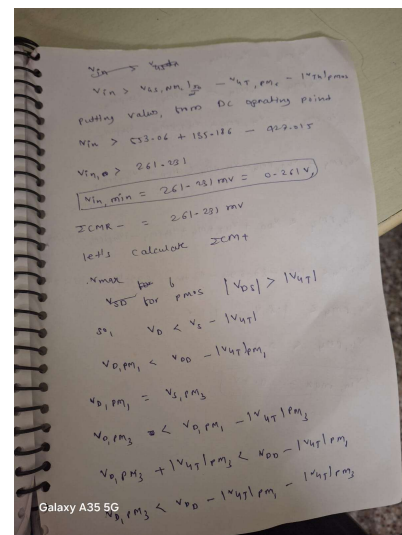
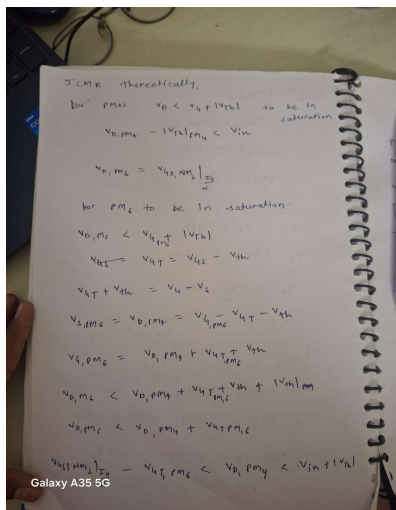


- Difference between diffamp input voltages

- At $\omega = \omega_{3dB}$, the peak input difference was **166.71 mV**
- At $\omega = \omega_{3dB}/10$, the peak input difference was only **14.92 mV**

6. Theoretical Calculations

Calculate and explain: ICMR+, ICMR-, CMRR, Gain, etc., using small-signal parameters from DC simulation.



CATER Calculation

$$CMRR = 20 \log \left| \frac{A_{dcm}}{A_{cm}} \right|$$

$$A_{dcm} = g_{m1} r_{m1} (R_{o1} || R_{o2})$$

$$R_{o1} = g_{m1} r_{m2} / g_{d1} r_{m2} g_{d1} r_{m2}$$

$$R_{o2} = g_{m2} r_{m1} / g_{d2} r_{m1} g_{d2} r_{m1}$$

$$A_{dcm} \rightarrow R_{o1} = \frac{7.16 \mu \times 10^{-3}}{925.136 \times 482 \times 10^{-12}}$$

$$R_{o1} = 35 \text{ K}\Omega$$

$$R_{o2} = \frac{5.66 \times 10^{-3}}{925.136 \times 10^{-12} \times 104.8 \times 10^{-6}}$$

$$R_{o2} = 340 \text{ K}\Omega$$

$$R_{o1} || R_{o2} = 31.93$$

$$A_{dcm} = 3.79 \times 31.93$$

$$A_{dcm} = 310.66$$

Galaxy A35 5G

$$A_{cm} = \frac{g_{m1} r_{d1n}}{(1 + 2R_{o2} g_{m1}) (1 + g_{m2} r_{d1n})}$$

$$\approx \frac{g_{m1}}{2R_{o2} g_{m1} g_{m2}}$$

$$A_{cm} \approx \frac{1}{2R_{o2} g_{m2}}$$

$$R_{o2} = \frac{g_{m1} r_{m1}}{g_{d1} r_{m1} \times g_{d1} r_{m1}}$$

$$R_{o2} = \frac{6.54 \times 10^{-3}}{700.431 \times 10^{-12} \times 1.33 \times 10^{-3}}$$

$$R_{o2} = 7.02 \text{ K}\Omega$$

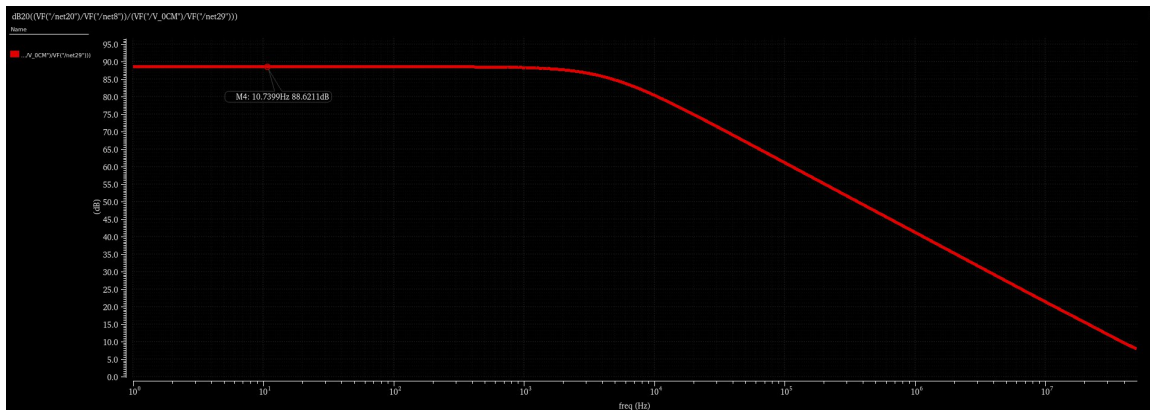
$$A_{cm} = \frac{1}{2 \times 7.02 \times 5.6}$$

$$A_{cm} = 0.0122$$

$$CMRR = 20 \log (310.66 \times 2 \times 7.02 \times 5.6)$$

$$CMRR \approx 83.78$$

Galaxy A35 5G



10. Conclusion

Theoretical and Simulated Results

The following parameters were computed both theoretically (using incremental parameters from DC operating point simulation) and verified through Cadence simulation.

Parameter	Theoretical Value	Simulated Value
ICMR ⁺	0.70 V	0.73 V
ICMR ⁻	0.261 V	0.49 V
CMRR	87.75 dB	88.6211 dB

11. References

EE610 Lectures

Thank You